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Robert
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT

In re application of: Kapre, et al

Attorney Docket No.: 01-721/LSI1P185

Application No.: 10/020,304

Examiner: Sefer, Ahmed N.

Filed: December 13, 2001

Group: 2826

Title: **BURIED CHANNEL DEVICES AND A
PROCESS FOR THEIR FABRICATION
SIMULTANEOUSLY WITH SURFACE
CHANNEL DEVICES TO PRODUCE
TRANSISTORS AND CAPACITORS WITH
MULTIPLE ELECTRICAL GATE OXIDES**

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail to: Commissioner for Patents, Washington, DC 20231 on November 22, 2002.

Signed: Natalie Morgan
Natalie Morgan

AMENDMENT B

Commissioner for Patents
Washington, D.C. 20231

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Dear Sir:

This amendment and the enclosed remarks are submitted in response to the Non-Final Office Action mailed on July 22, 2002. Applicants respectfully request reconsideration of the captioned application in view of the following remarks and amendments.

In the Claims:

Please amend the claims as follows (a version of the amended claims showing the changes made accompanies this response in an Appendix):

1. (Once Amended) ~~In a semiconductor device having at least an insulating gate dielectric layer and a gate fabricated upon a semiconductor substrate, a buried channel implanted below the insulating gate dielectric layer, the buried channel being doped with a predetermined dopant and a peak concentration of the dopant positioned at a~~

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02 FC:1202 90.00 CH
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